



2SB1202/2SD1802

High-Current Switching Applications

Applications

- Voltage regulators, relay drivers, lamp drivers, electrical equipment.

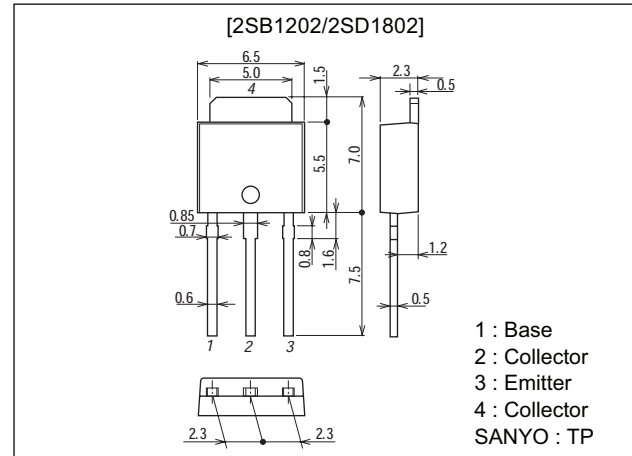
Features

- Adoption of FBET, MBIT processes.
- Large current capacity and wide ASO.
- Low collector-to-emitter saturation voltage.
- Fast switching speed.
- Small and slim package making it easy to make 2SB1202/2SD1802-used sets smaller.

Package Dimensions

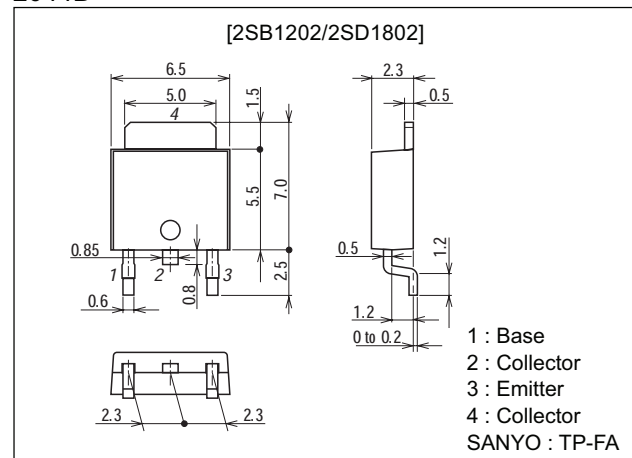
unit:mm

2045B



unit:mm

2044B



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SANYO Electric Co.,Ltd. Semiconductor Company

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2SB1202/2SD1802

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Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(-)-60	V
Collector-to-Emitter Voltage	V_{CEO}		(-)-50	V
Emitter-to-Base Voltage	V_{EBO}		(-)-6	V
Collector Current	I_C		(-)-3	A
Collector Current (Pulse)	I_{CP}		(-)-6	A
Collector Dissipation	P_C		1	W
		$T_c=25^\circ\text{C}$	15	W
Junction Temperature	T_J		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

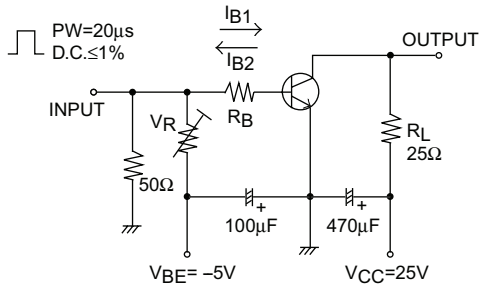
Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40\text{V}, I_E=0$			(-)-1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4\text{V}, I_C=0$			(-)-1	μA
DC Current Gain	h_{FE1}	$V_{CE}=(-)2\text{V}, I_C=(-)100\text{mA}$	100*		560*	
	h_{FE2}	$V_{CE}=(-)2\text{V}, I_C=(-)3\text{A}$	35			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10\text{V}, I_C=(-)50\text{mA}$		150		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)10\text{V}, f=1\text{MHz}$		(39)25		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)2\text{A}, I_B=(-)100\text{mA}$		0.19	0.5	V
				(-)-0.35	(-)-0.7	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)2\text{A}, I_B=(-)100\text{mA}$		(-)-0.94	(-)-1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu\text{A}, I_E=0$	(-)-60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1\text{mA}, R_{BE}=\infty$	(-)-50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu\text{A}, I_C=0$	(-)-6			V
Turn-ON Time	t_{on}	See specified Test Circuit		70		ns
Storage Time	t_{stg}	See specified Test Circuit		(450)		ns
				650		ns
Fall Time	t_f	See specified Test Circuit		35		ns

* : The 2SB1202/2SD1802 are classified by 100mA h_{FE} as follows :

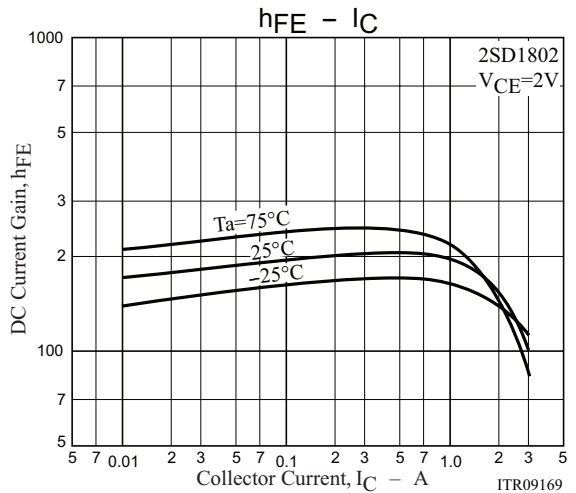
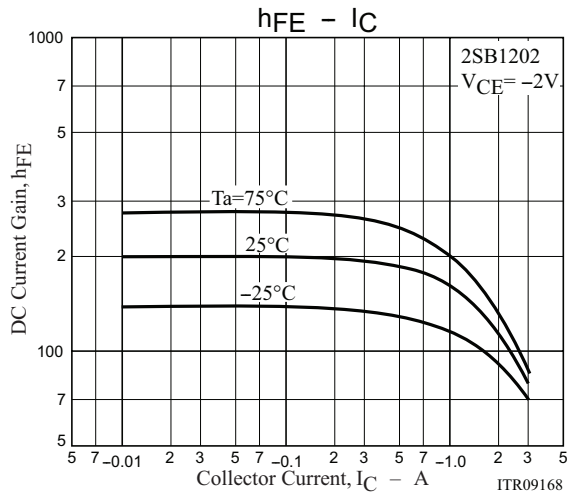
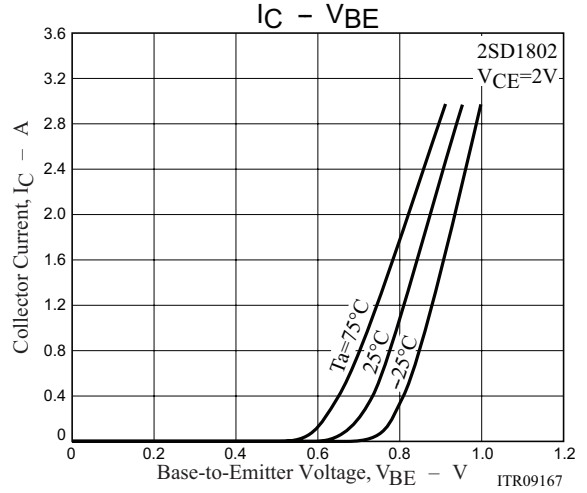
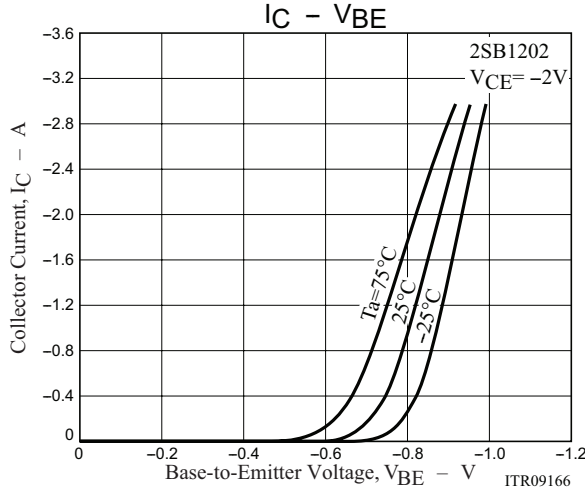
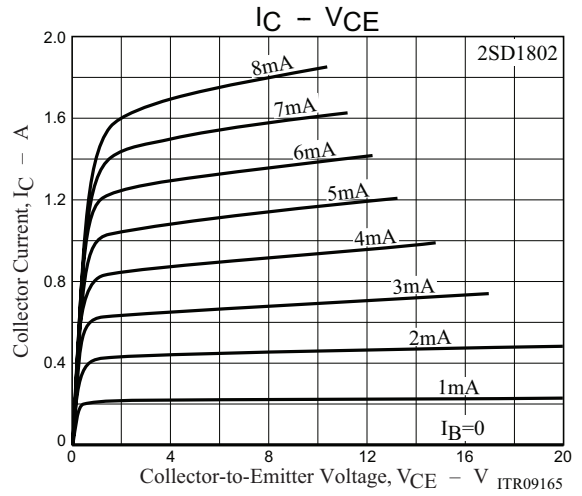
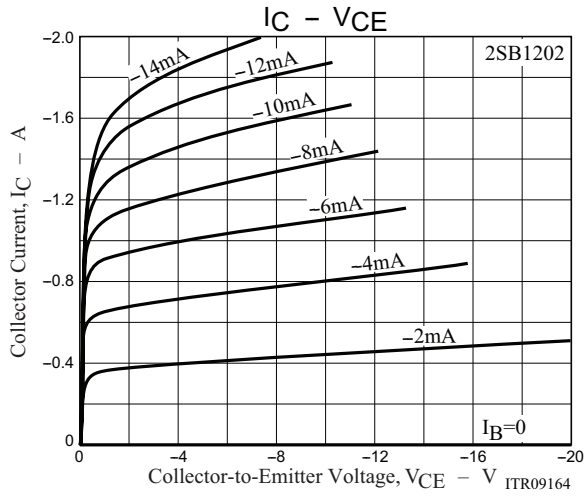
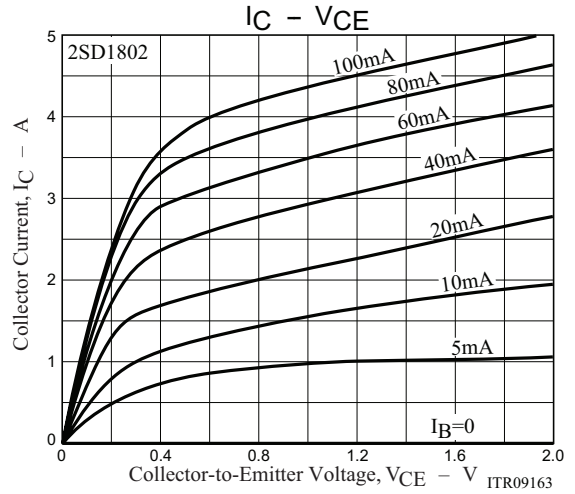
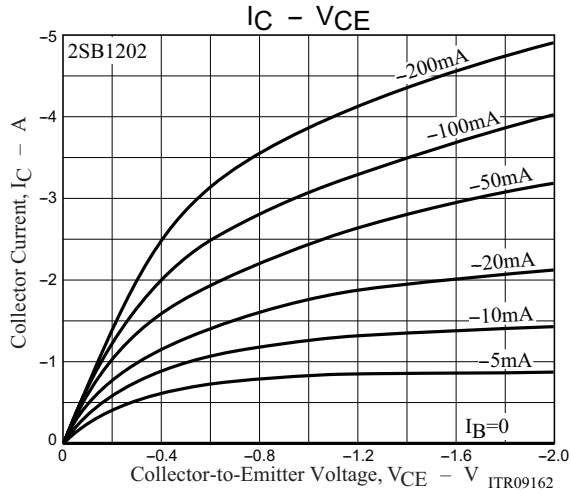
Rank	R	S	T	U
h_{FE}	100 to 200	140 to 280	200 to 400	280 to 560

Switching Time Test Circuit

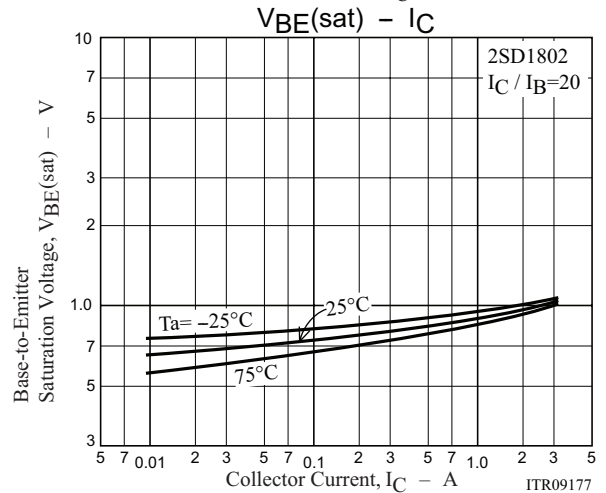
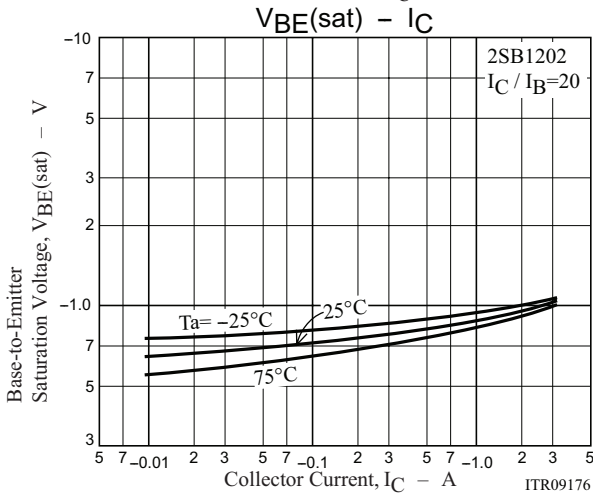
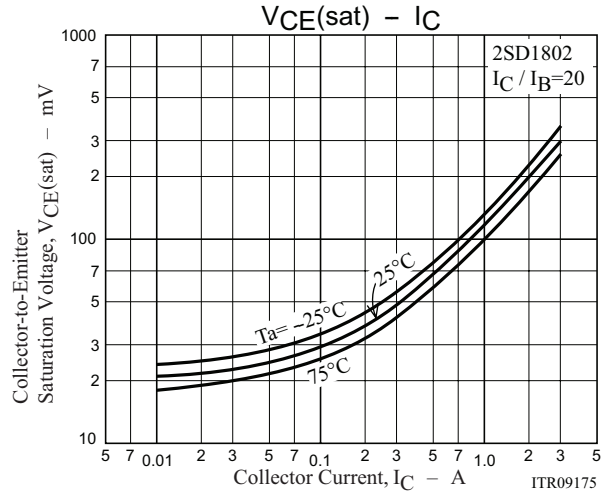
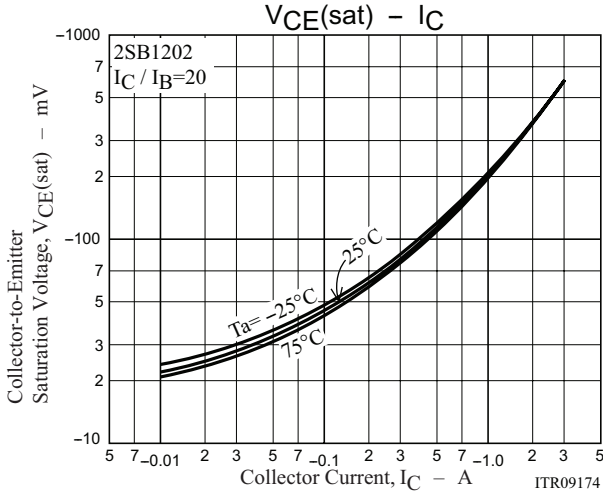
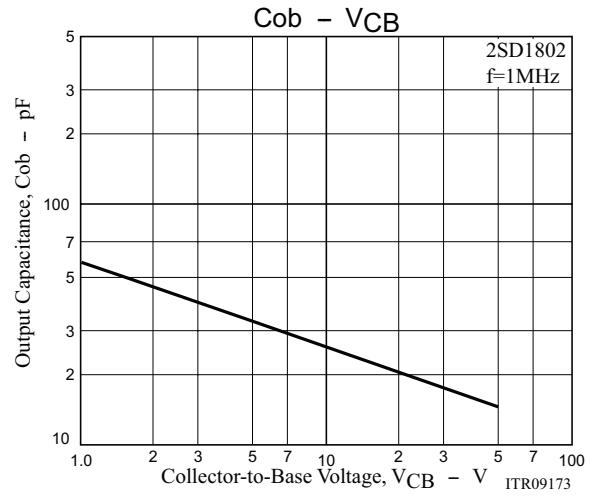
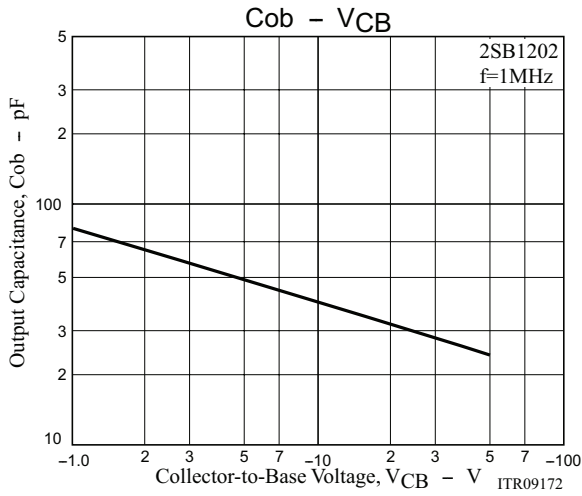
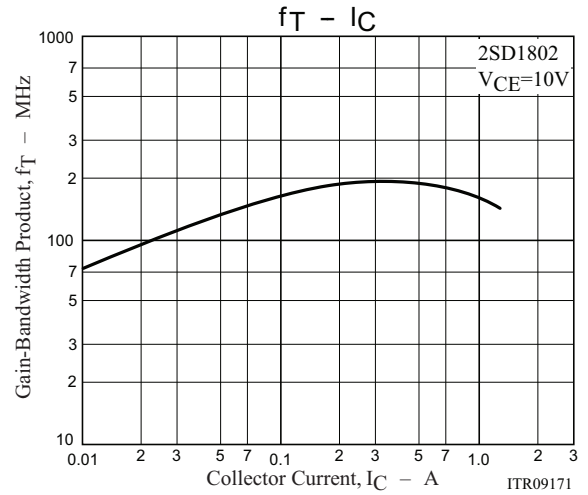
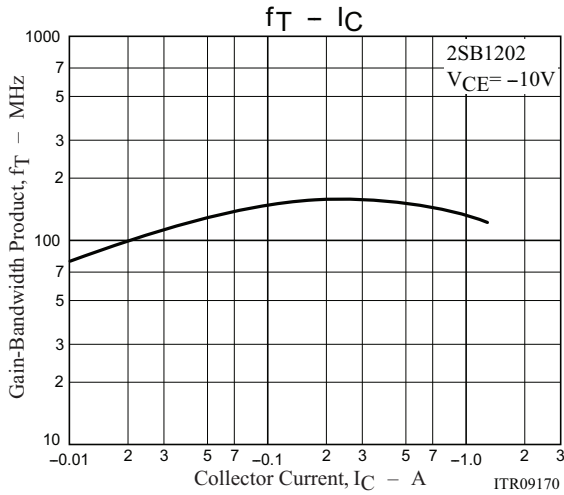


$I_C=10I_{B1} = -10I_{B2}=1\text{A}$
 (For PNP, the polarity is reversed.)

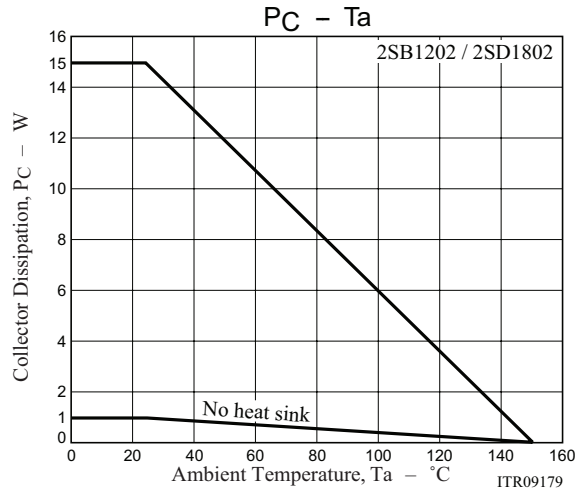
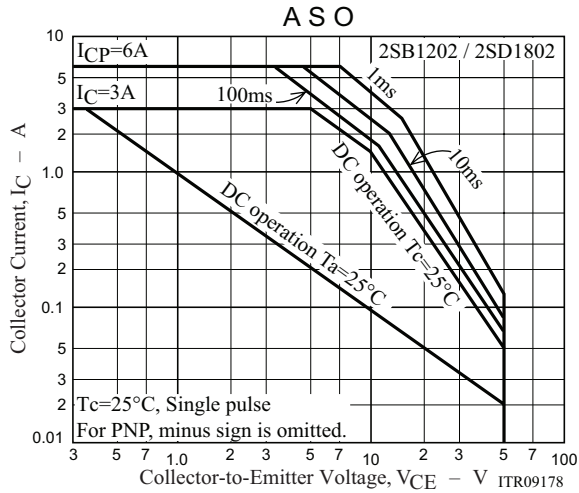
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